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Vishay Semiconductors

COMPLIANT

HALOGEN FREE

Thyristor, Surface-Mount, Phase Control SCR, 16 A



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{T(AV)}	16 A				
V _{DRM} /V _{RRM}	1200 V				
V_{TM}	1.25 V				
I _{GT}	45 mA				
T _J	-40 to +125 °C				
Package	D ² PAK 2L (TO-263AB 2L)				
Circuit configuration	Single SCR				

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified
- Meets JESD 201 class 2 whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-25TTS12S2LHM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per

J-STD-002

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS							
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5					
Aluminum IMS, R _{thCA} = 15 °C/W	A						
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	16.5	25.0					

Note

• $T_A = 55$ °C, $T_J = 125$ °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	16	۸			
I _{RMS}		25	- A			
V _{RRM} /V _{DRM}		1200	V			
I _{TSM}		350	Α			
V _T	16 A, T _J = 25 °C	1.25	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
T _J		-40 to +125	°C			

VOLTAGE RATINGS								
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} / I _{DRM} , AT 125 °C mA					
VS-25TTS12S2LHM3	1200	1200	10					



ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS		
PANAIVIETEN	STINIBUL	163	TEST CONDITIONS		MAX.	UNITS		
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° c	onduction half sine wave	1	6			
Maximum RMS on-state current	I _{RMS}			2	5	Α		
Maximum peak, one-cycle,	I	10 ms sine pulse, r	rated V _{RRM} applied	30	00	^		
non-repetitive surge current	I _{TSM}	10 ms sine pulse, r	no voltage reapplied	35	50			
Maximum I ² t for fusing	l ² t	10 ms sine pulse, r	rated V _{RRM} applied	45	50	A ² s		
Maximum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied		63	30	A-5		
Maximum I ² √t for fusing	I²√t	t = 0.1 ms to 10 ms	s, no voltage reapplied	6300		A²√s		
Maximum on-state voltage drop	V_{TM}	16 A, T _J = 25 °C		1.25		V		
On-state slope resistance	r _t	T 405 00		12	2.0	mΩ		
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1.	.0	V		
Maximum reverse and direct leakage current		T _J = 25 °C	V _R = Rated V _{RRM} /V _{DRM}	0.	.5			
waximum reverse and direct leakage current	I _{RM} / I _{DM}	T _J = 125 °C	VR = Nateu VRRM/ VDRM	1	0			
Holding current	I _H	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	-	150	mA		
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C		Anode supply = 6 V, resistive load, T _J = 25 °C		20	00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = open$		$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = open$ 500		00	V/µs	
Maximum rate of rise of turned-on current	di/dt					15	50	A/μs

TRIGGERING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum peak gate power	P _{GM}		8.0	W			
Maximum average gate power	P _{G(AV)}		2.0	l vv			
Maximum peak positive gate current	+l _{GM}		1.5	Α			
Maximum peak negative gate voltage	-V _{GM}		10	V			
		Anode supply = 6 V, resistive load, T _J = -10 °C	60	mA			
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	45				
		Anode supply = 6 V, resistive load, T _J = 125 °C	20				
		Anode supply = 6 V, resistive load, T _J = -10 °C	2.5				
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	V			
		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V			
Maximum DC gate voltage not to trigger	V_{GD}	T 105 °C V reted value	0.25				
Maximum DC gate current not to trigger	I_{GD}	$T_J = 125$ °C, $V_{DRM} = $ rated value	2.0	mA			

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9				
Typical reverse recovery time	t _{rr}	T _{.I} = 125 °C	4	μs			
Typical turn-off time	t _q	1	110				



THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C			
Soldering temperature	T _S	For 10 s (1.6 mm from case)	260	C			
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.1				
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	°C/W			
Approximate weight			2	g			
Approximate weight			0.07	OZ.			
Marking device		Case style: 2L D ² PAK (2L TO-263AB)	25TTS	12SH			

Note

 $^{^{(1)}}$ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μ m] copper 40 °C/W

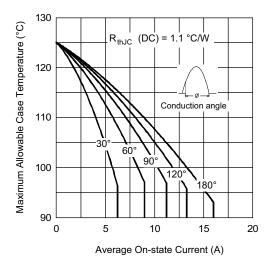


Fig. 1 - Current Rating Characteristics

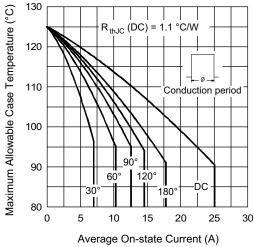


Fig. 2 - Current Rating Characteristics

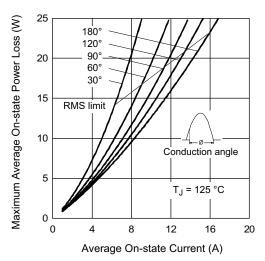


Fig. 3 - On-State Power Loss Characteristics

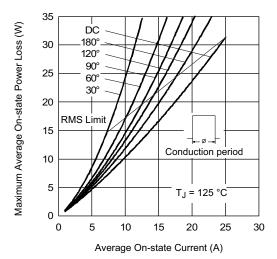


Fig. 4 - On-State Power Loss Characteristics



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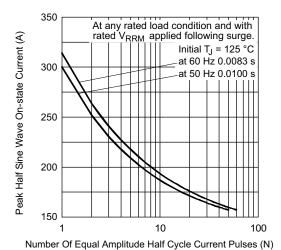


Fig. 5 - Maximum Non-Repetitive Surge Current

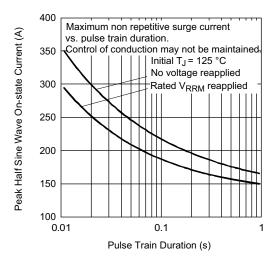


Fig. 6 - Maximum Non-Repetitive Surge Current

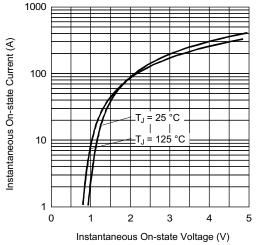


Fig. 7 - On-State Voltage Drop Characteristics

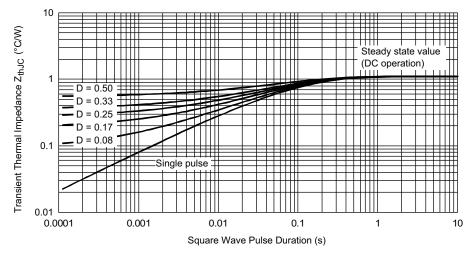


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

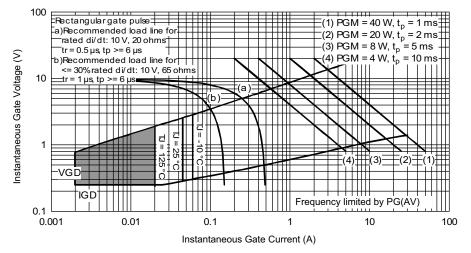
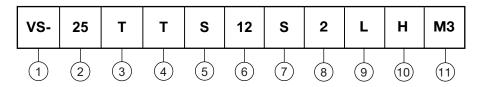


Fig. 9 - Gate Characteristics



ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Current rating (25 = 25 A)
- Circuit configuration:
 - T = single thyristor
- 4 Package:
 - $T = D^2PAK (TO-263AB)$
- 5 Type of silicon:
 - S = standard recovery rectifier
- 6 Voltage rating: voltage code x 100 = V_{RRM} 12 = 1200 V
- 7 S = surface mountable
- 9 L = tape and reel (left oriented), for different orientation contact factory
- 10 H = AEC-Q101 qualified
- M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

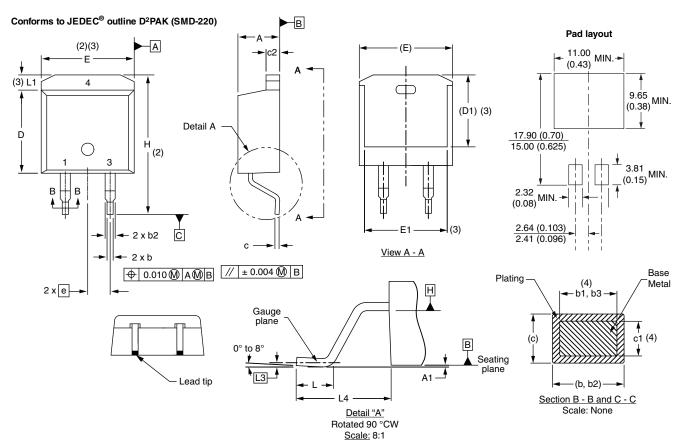
ORDERING INFORMATION (Example)						
PREFERRED P/N QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-25TTS12S2LHM3	800	800	13" diameter reel			

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96683</u>				
Part marking information <u>www.vishay.com/doc?96693</u>				
Packaging information	www.vishay.com/doc?96317			



D²PAK 2L (TO-263AB 2L)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	MILLIMETERS		INCHES	
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
D1	6.86	8.00	0.270	0.315	3	
Е	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100 BSC			
Н	14.61	15.88	0.575	0.625		
L	1.78	2.79	0.070	0.110		
L1	-	1.65	-	0.066	3	
L3	0.25	0.25 BSC		BSC		
L4	4.78	5.28	0.188	0.208		

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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